

	Type	Hits	Search Text
1	BRS	1	438/300.ccls. and 438/421.ccls.
2	BRS	784	438/300.ccls. or 438/421.ccls. or 438/197.ccls. or 438/218.ccls. or 438/422.ccls.
3	BRS	1551	((rais\$2 or elevat\$2) near2 (source or drain)) and (transistor or FET or MOSFET)
4	BRS	320	((rais\$2 or elevat\$2) near2 (source or drain)) and (transistor or FET or MOSFET)) and (air or vacuum or gap)
5	IS&R	1	("5977561").PN.
6	IS&R	6	(("5693974") or ("5736446") or ("5914519") or ("5977561") or ("5319232") or ("6127711")).PN.
7	BRS	1409	(polysilicon near2 gate) and ((phosphorous or phosphoruos or phosphorus or P) near2 (doped or implanted) with gate)
8	BRS	622	(polysilicon near2 gate) and ((phosphorous or phosphoruos or phosphorus or P) near2 (doped or implanted) near4 gate)
9	BRS	148	(polysilicon near gate) and ((phosphorous or phosphoruos or phosphorus or P) near (doped or implanted) near2 gate)
10	BRS	78	(polysilicon near gate) same ((phosphorous or phosphoruos or phosphorus or P) near (doped or implanted) near2 gate)
11	BRS	75	(polysilicon near gate) with ((phosphorous or phosphoruos or phosphorus or P) near (doped or implanted) near2 gate)
12	BRS	321	pocket adj implant
13	BRS	291	S17 and source and drain
14	BRS	279	S18 and (FET or MOSFET or transistor or TFT)

	DBs
1	USPAT
2	USPAT
3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	USPAT; USOCR
6	USPAT; USOCR
7	USPAT
8	USPAT
9	USPAT
10	USPAT
11	USPAT
12	USPAT
13	USPAT
14	USPAT